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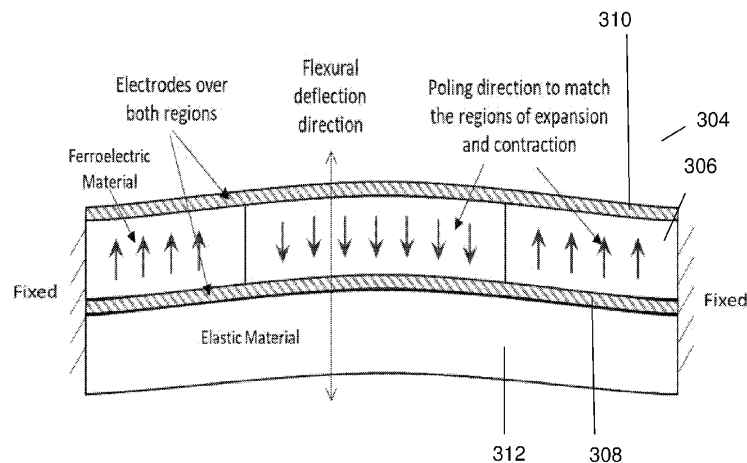
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(54) Title: **PIEZOELECTRIC DEVICE AND METHOD OF FORMING THE SAME**

FIG. 3



(57) Abstract: Various embodiments may relate to a piezoelectric device. The piezoelectric device may include a substrate, and a layered stacked arrangement anchored to the substrate. The layered stacked arrangement may include a piezoelectric layer. The stacked arrangement may also include a first electrode on a first side of the piezoelectric layer. The stacked arrangement may further include a second electrode on a second side of the piezoelectric layer opposite the first side. The piezoelectric layer may include a first region including one or more dipole domains of a first type, and one or more dipole domains of a second type. The first electrode may be at least partially in contact with the first region and at least partially in contact with the second region. The second electrode may be at least partially in contact with the first region and at least partially in contact with the second region.

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